



Second Call for Papers

2011 International Conference on Simulation of Semiconductor Processes and Devices
SISPAD2011

September 8 – 10, 2011

Tokyo International Exchange Center, Tokyo, JAPAN

<http://www.si.eei.eng.osaka-u.ac.jp/sispad/2011/>

Co-sponsored by
Technical co-sponsored by
In cooperation with

Japan Society of Applied Physics
IEEE Electron Devices Society
IEEE EDS Japan Chapter
IEEE EDS Kansai Chapter
The Institute of Electronics, Information and Communication Engineers



Scope:

This conference provides an opportunity for the presentation and discussion of the latest advances in modeling and simulation of semiconductor devices, processes, and equipments for integrated circuits.

Topics:

- Simulation and modeling based on continuum and/or particle methods for all sorts of devices including next generation CMOS devices, emerging memory devices, optoelectronic devices, lasers, TFTs, organic electronic devices, micro/nano sensors, power electronic devices and other semiconductor-based "green" devices, spintronics devices, tunnel FETs, SETs, carbon-based nanodevices, molecular devices, and bioelectronic devices.
- Fundamental aspects of device modeling and simulation such as quantum transport, fluctuation, noise, and reliability issues.
- All sorts of process simulations and modeling based on continuum and/or atomistic approaches, including the first-principles material design and growth simulation of nano-scale fabrication.
- Compact modeling for circuit simulation, including high frequency applications.
- Process/device/circuit simulation in context with system design and verification.
- Equipment, topography, lithography modeling and algorithms.
- Interconnect modeling and algorithm including noise and parasitic effects.
- Advanced numerical methods and algorithms including grid generation, user-interface, and visualization.
- High precision metrology for the modeling of semiconductor devices and processes.

Abstract Submission:

Authors should send a **PDF file of a two-page abstract** (A4 size or 22x28 cm) including figures, and a **reply form** by e-mail.

- A PDF file must be smaller than 3MByte.
- The text of the abstract should be typed single-spaced, one column per page.
- 10 - 12 point font is recommended.
- To avoid unexpected troubles in reviewing processes, you can NOT use the following fonts in the texts, graphs or figures.
 - 2 byte font such as Japanese, Korean, Chinese characters.
 - 1 byte font of Asian characters such as MS Gothic, MS Mincho, Ryumin, Batang etc.
- Use the black and white images because the abstract will be printed in black and white for review.

Detailed information will be updated in the web site:

<http://www.si.eei.eng.osaka-u.ac.jp/sispad/2011>

Please note that a postal submission in hard copy will NOT be accepted.

Authors of accepted papers will be notified by **May 19, 2011**. Camera-ready copy of a four-page manuscript will be required from the authors for the Conference Proceedings by **June 30, 2011**.

Deadline for submission of abstract: **March 1, 2011**

The abstract should be sent electronically to:

e-mail: sispad-prog2011@si.eei.eng.osaka-u.ac.jp

Announcement of Special Events:

Companion Workshop on September 7, 2011 is now in the planning stage.

Organization:

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